

## N- and P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
	V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
N-Channel	20	0.060 at V <sub>GS</sub> = 4.5 V	3.4
		0.070 at V <sub>GS</sub> = 2.5 V	3.2
		0.100 at V <sub>GS</sub> = 1.8 V	2.5
P-Channel	- 20	0.110 at V <sub>GS</sub> = - 4.5 V	- 2.5
		0.145 at V <sub>GS</sub> = - 2.5 V	- 2.0
		0.220 at V <sub>GS</sub> = - 1.8V	- 1.0

### FEATURES

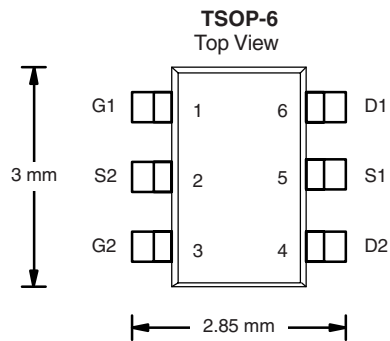
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Fast Switching In Small Footprint
- Very Low R<sub>DS(on)</sub> for Increased Efficiency
- Compliant to RoHS Directive 2002/95/EC



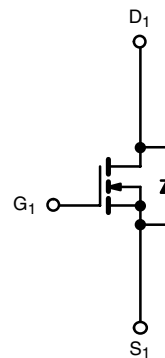
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

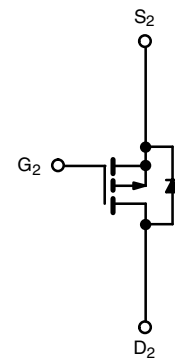
- Load Switch for Portable Devices



Ordering Information: Si3586DV-T1-E3 (Lead (Pb)-free)  
Si3586DV-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		5 s	Steady State	5 s	Steady State		
Drain-Source Voltage	V <sub>DS</sub>	20		- 20		V	
Gate-Source Voltage	V <sub>GS</sub>	± 8					
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	3.4	2.9	- 2.5	- 2.1	A
		T <sub>A</sub> = 70 °C	2.7	2.3	- 2.0	- 1.7	
Pulsed Drain Current	I <sub>DM</sub>	± 8				W	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	1.05	0.75	- 1.05	- 0.75		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	1.15	0.83	1.15	0.83	W
		T <sub>A</sub> = 70 °C	0.73	0.53	0.73	0.53	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	R <sub>thJA</sub>	93	110	°C/W
	Steady State		130	150	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	90	90	

Note:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Static</b>							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.40	1.1	V	
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.40	-1.1		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$	N-Ch		$\pm 100$	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$	P-Ch		$\pm 100$		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	N-Ch		1	$\mu\text{A}$	
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$	P-Ch		-1		
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	N-Ch		10		
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	P-Ch		-10		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	N-Ch	5		A	
		$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	-5			
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 3.4\text{ A}$	N-Ch		0.047	$\Omega$	
		$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$	P-Ch		0.086		
		$V_{GS} = 2.5\text{ V}, I_D = 3.2\text{ A}$	N-Ch		0.054		0.070
		$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$	P-Ch		0.116		
		$V_{GS} = -1.8\text{ V}, I_D = -2.5\text{ A}$	N-Ch		0.075		0.100
		$V_{GS} = -1.8\text{ V}, I_D = -1.0\text{ A}$	P-Ch		0.170		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 5\text{ V}, I_D = 3.4\text{ A}$	N-Ch		13	S	
		$V_{DS} = -5\text{ V}, I_D = -2.5\text{ A}$	P-Ch		6		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.05\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.8	V	
		$I_S = -1.05\text{ A}, V_{GS} = 0\text{ V}$	P-Ch		-0.8		
<b>Dynamic<sup>b</sup></b>							
Total Gate Charge	$Q_g$	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 3.4\text{ A}$  P-Channel $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$	N-Ch		4.1	6.0	nC
Gate-Source Charge	$Q_{gs}$		N-Ch		0.65		
			P-Ch		0.68		
Gate-Drain Charge	$Q_{gd}$	N-Ch		0.8			
		P-Ch		1.3			
Gate Resistance	$R_g$		N-Ch		2.6		$\Omega$
			P-Ch		9.8		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 6\text{ }\Omega$	N-Ch		30	45	ns
Rise Time	$t_r$		N-Ch		52	85	
		P-Ch		55	85		
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$	N-Ch		25	40	
			P-Ch		55	85	
Fall Time	$t_f$	N-Ch		20	30		
		P-Ch		32	50		
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.05\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		25	40	
		$I_F = -1.05\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	P-Ch		25	40	

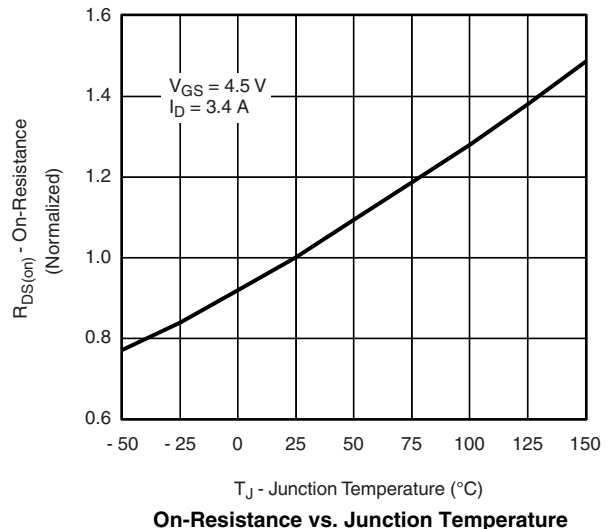
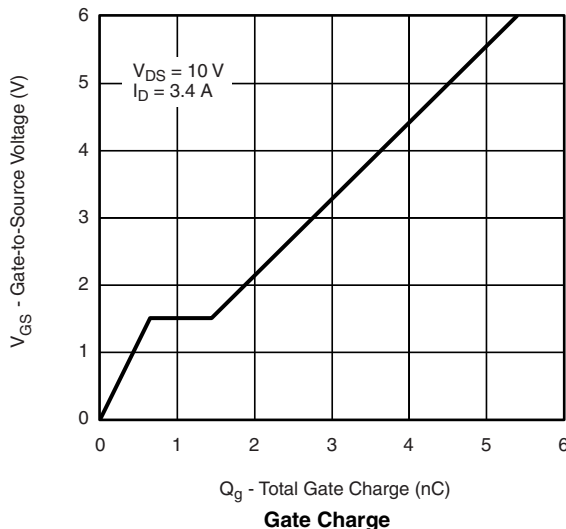
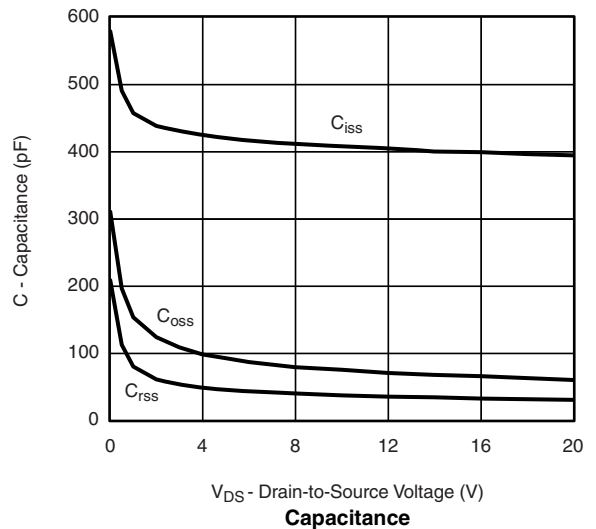
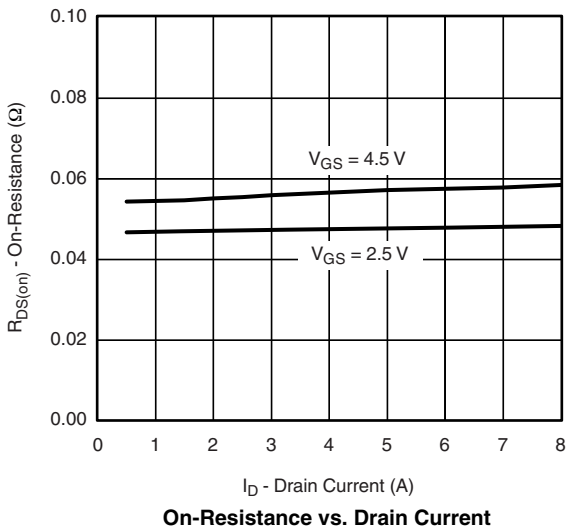
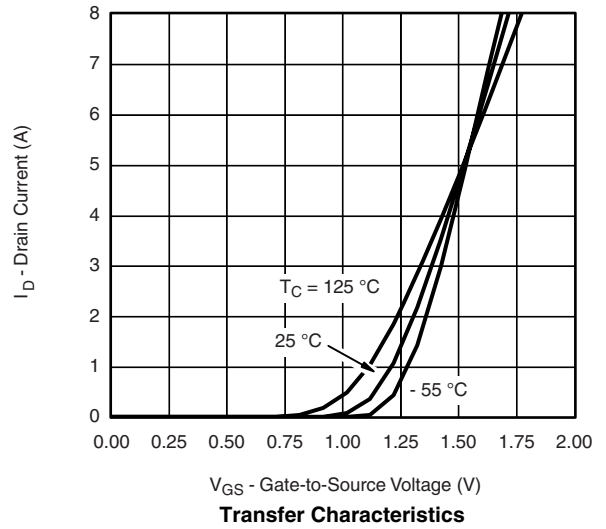
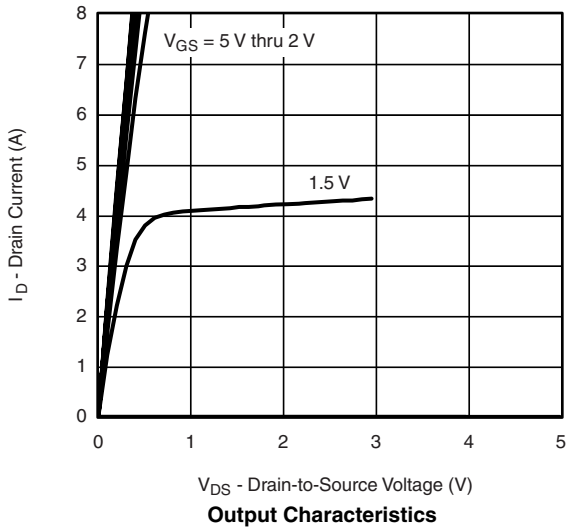
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

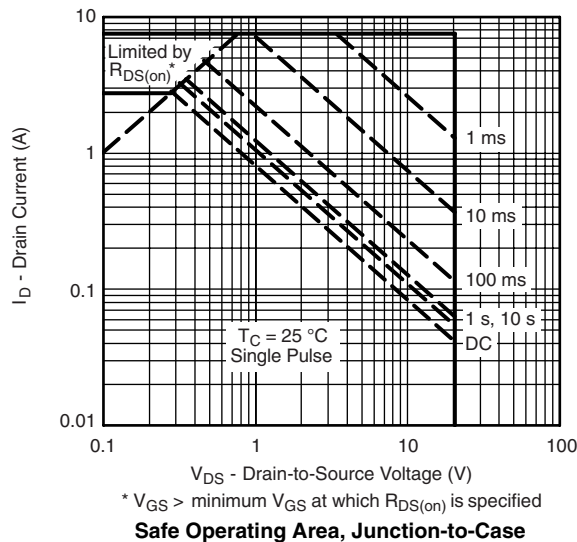
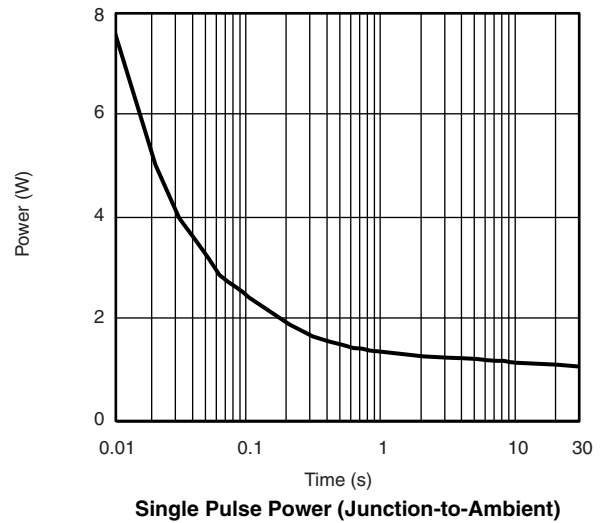
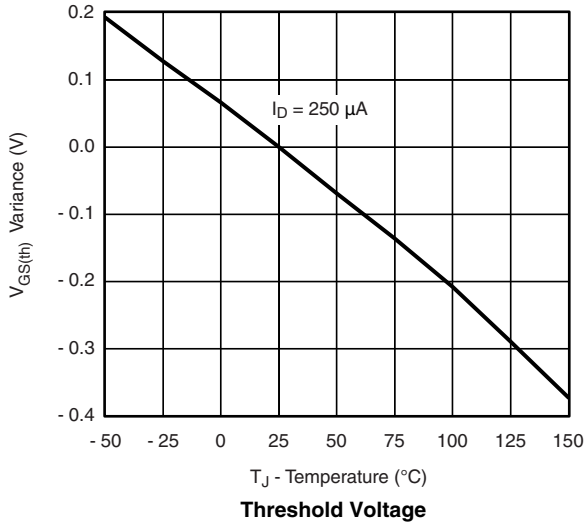
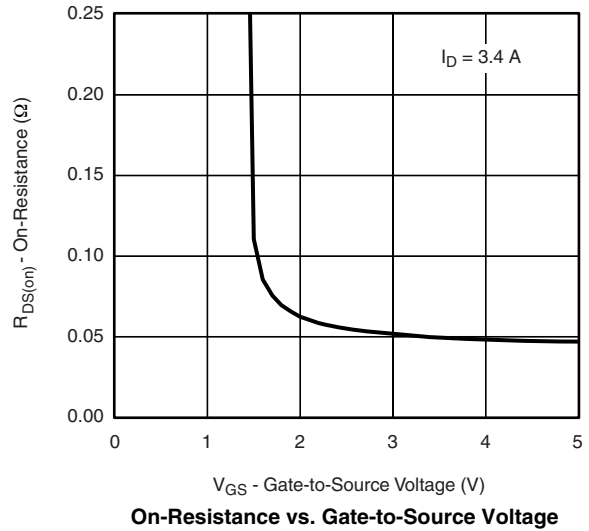
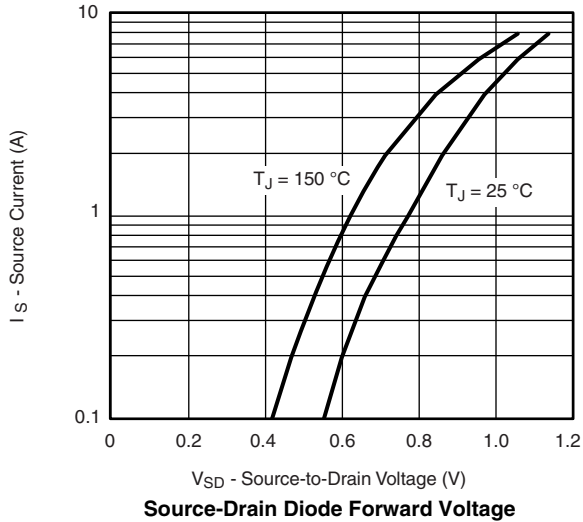
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

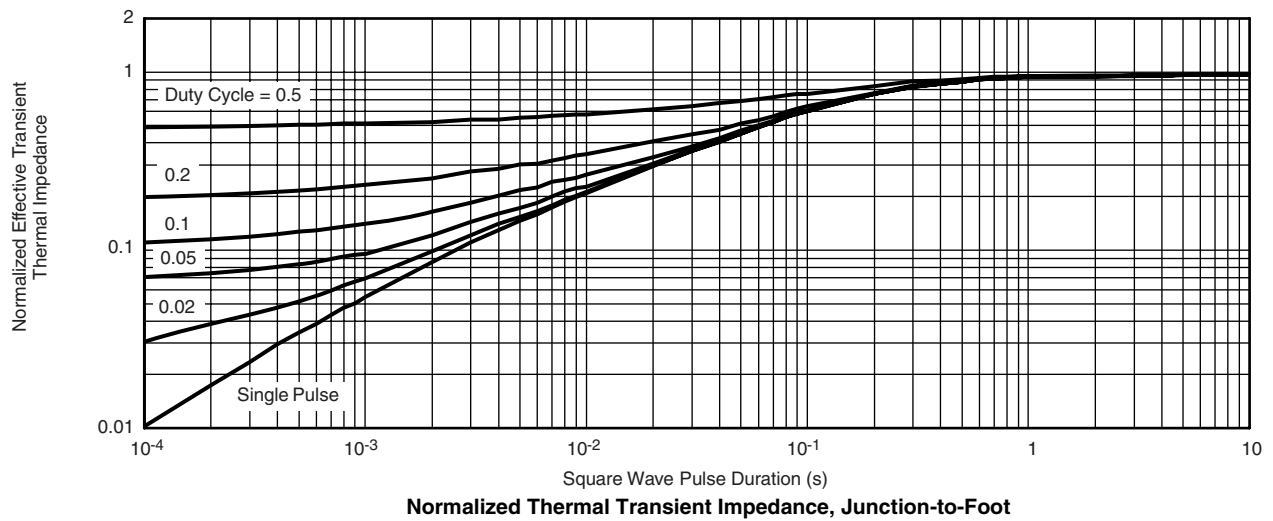
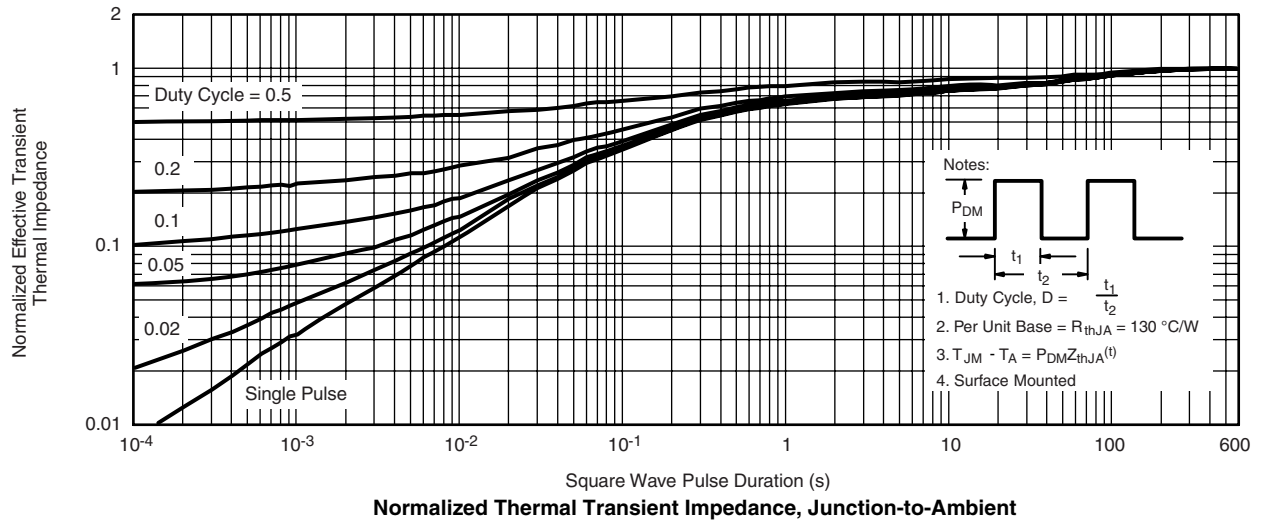
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



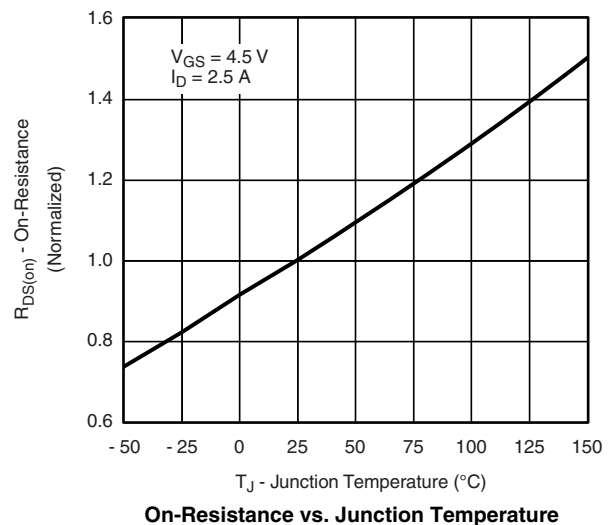
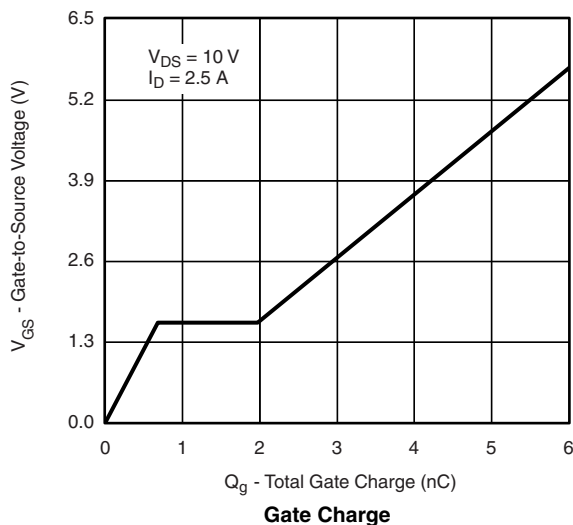
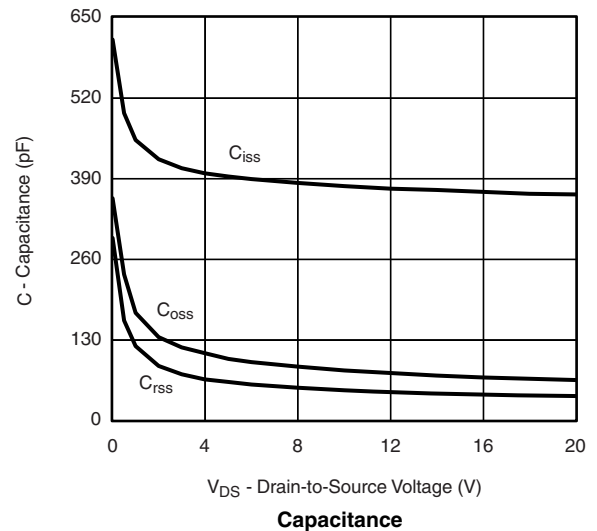
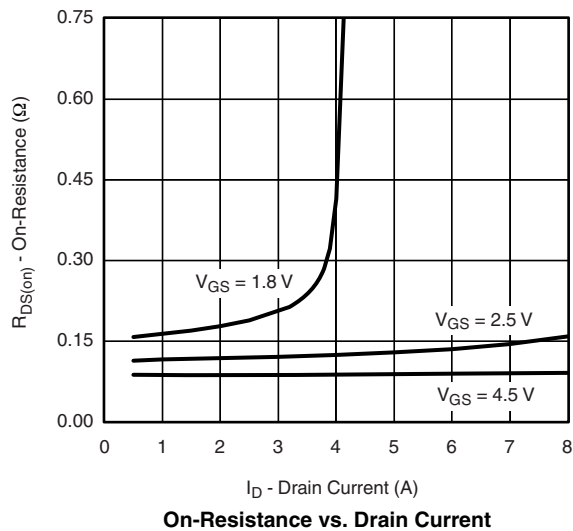
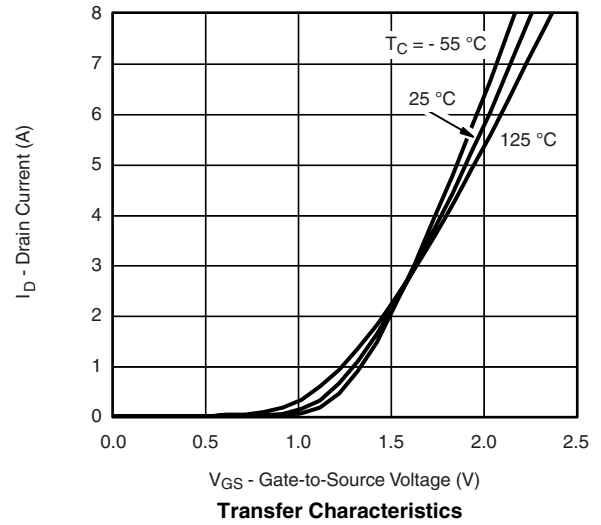
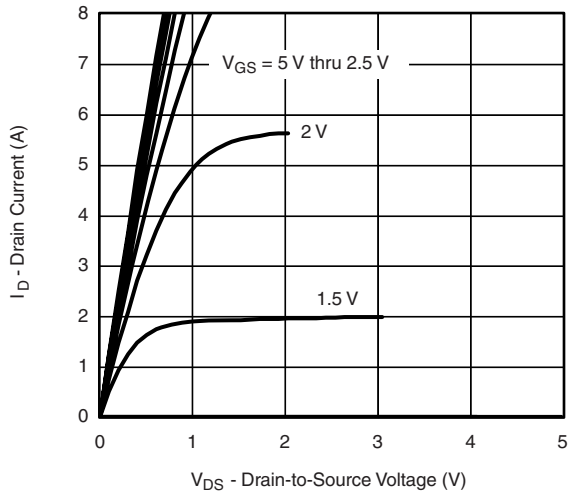
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



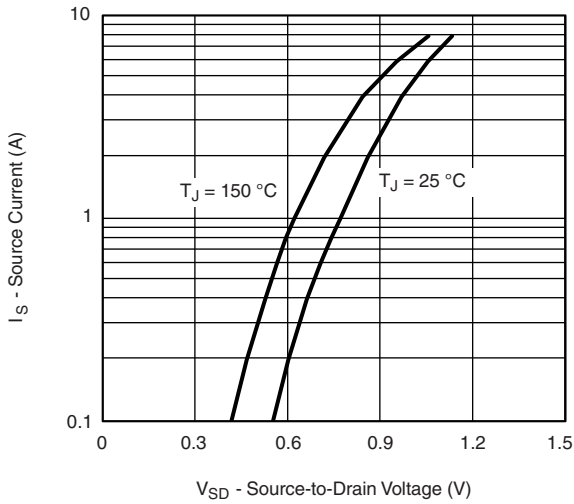
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



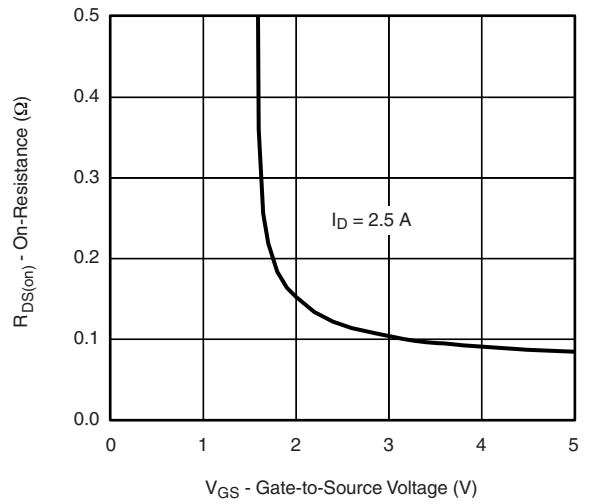
## P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



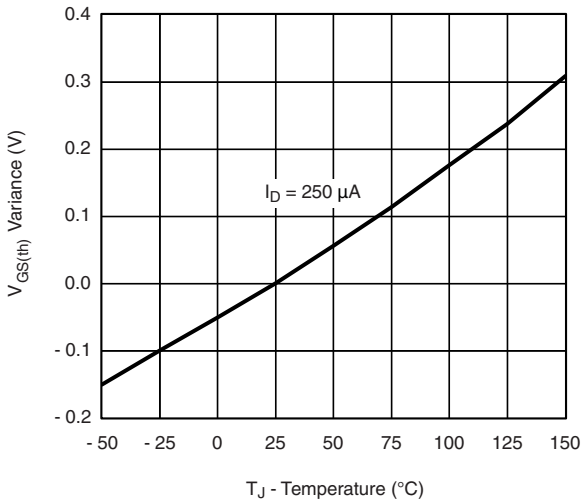
**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



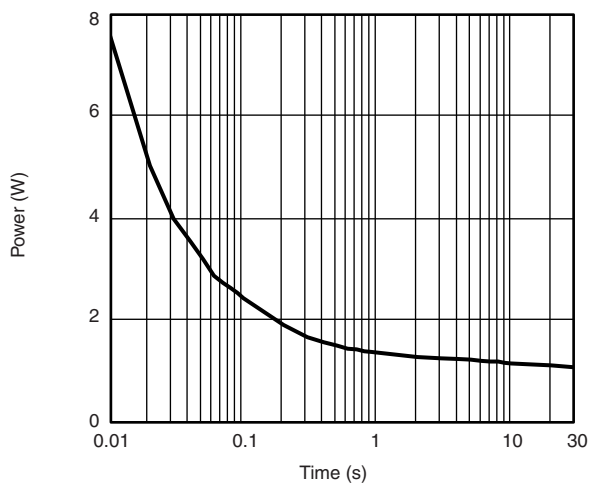
**Source-Drain Diode Forward Voltage**



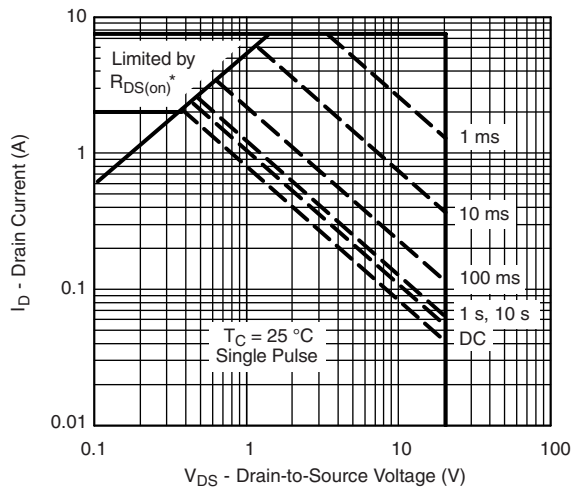
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



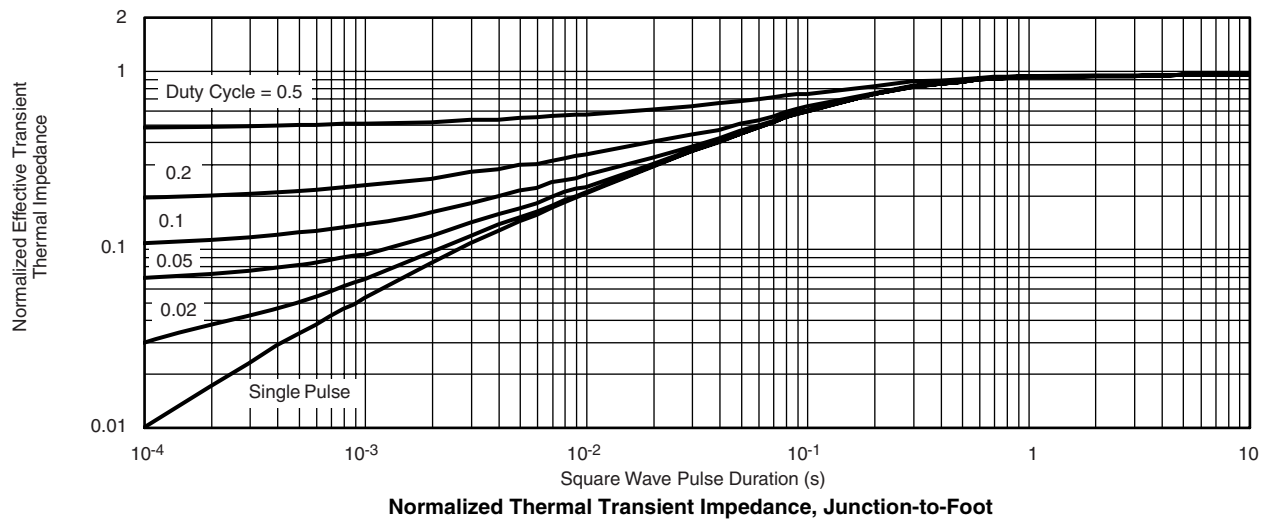
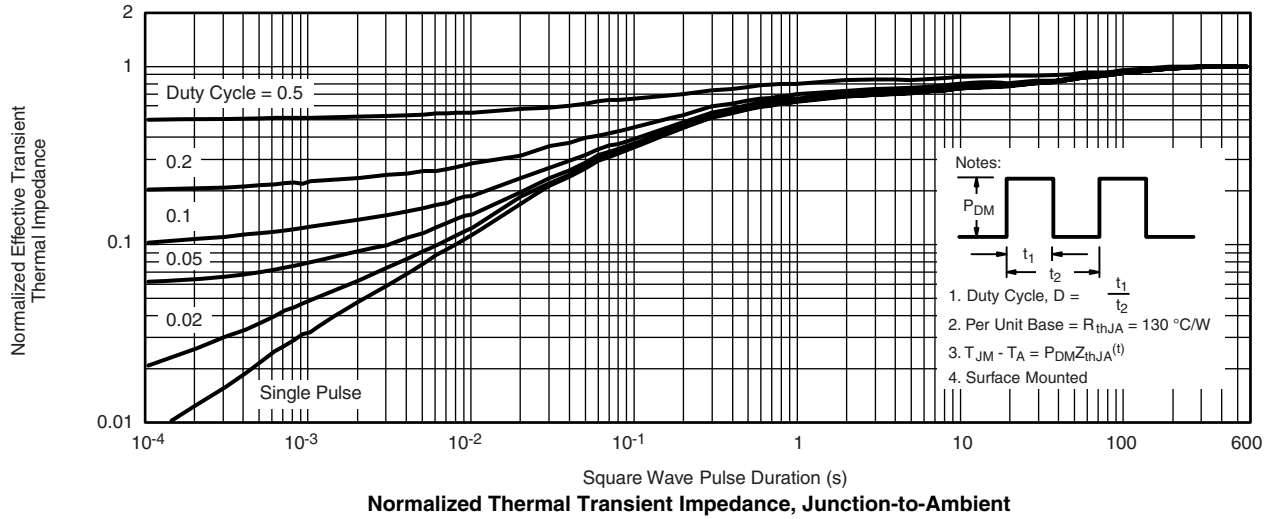
**Single Pulse Power (Junction-to-Ambient)**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Case**

**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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